![Truesemi logo]

TSP7N65M/TSF7N65M
650V N-Channel MOSFET

General Description

This Power MOSFET is produced using Truesemi's advanced planar stripe DMOS technology.
This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency switched mode power supplies, active power factor correction based on half bridge topology.

Features

- 7A,650V,Max.$R_{DS(on)}$=1.6Ω @ V_{GS} =10V
- Low gate charge(typical 29nC)
- High ruggedness
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability

TO-220   TO-220F

G D S   G D S
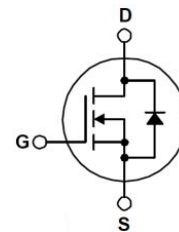
Absolute Maximum Ratings T_C=25℃ unless otherwise specified

Symbol	Parameter		TSP7N65M	TSF7N65M	Units
V_{DSS}	Drain-Source Voltage		650		V
V_{GS}	Gate-Source Voltage		± 30		V
I_D	Drain Current	T_C = 25℃	7	7*	A
		T_C = 100℃	4.5	4.5*	A
I_{DM}	Pulsed Drain Current (Note 1)		30	30*	A
E_{AS}	Single Pulsed Avalanche Energy (Note 2)		260		mJ
E_{AR}	Repetitive Avalanche Energy (Note 1)		14.7		mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)		4.5		V/ns
P_D	Power Dissipation (T_C = 25℃)		147	48	W
	-Derate above 25℃		1.18	0.38	W/℃
T_J, T_{STG}	Operating and Storage Temperature Range		-55 to +150		℃
T_L	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds		300		℃

* Drain current limited by maximum junction temperature.

Thermal Resistance Characteristics

Symbol	Parameter	TSP7N65M	TSF7N65M	Units
$R_{\theta JC}$	Thermal Resistance,Junction-to-Case	0.85	2.6	℃/W
$R_{\theta CS}$	Thermal Resistance,Case-to-Sink Typ.	0.5	--	℃/W
$R_{\theta JA}$	Thermal Resistance,Junction-to-Ambient	62.5	62.5	℃/W

Electrical Characteristics T_C=25 ℃ unless otherwise specified

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}$, I_D = 250 uA	3.0	--	5.0	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS} = 10 V, I_D = 3.75A	--	1.2	1.6	Ω
Off Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS} = 0 V, I_D = 250 uA	650	--	--	V
△BVDSS / △TJ	Breakdown Voltage Temperature Coefficient	ID = 250 uA, Referenced to 25 ℃	--	0.7		V/℃
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 650 V, V_{GS} = 0 V	--	--	1	uA
		V_{DS} = 520 V, T_J = 125℃	--	--	10	uA
I_{GSSF}	Gate-Body Leakage Current,Forward	V_{GS} = 30 V, V_{DS} = 0 V	--	--	100	nA
I_{GSSR}	Gate-Body Leakage Current,Reverse	V_{GS} =- 30 V, V_{DS} = 0 V	--	--	-100	nA
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS} = 25 V, V_{GS} = 0 V, f = 1.0 MHz	--	1200	--	pF
C_{oss}	Output Capacitance		--	110	--	pF
C_{rss}	Reverse Transfer Capacitance		--	12.6	--	pF
Switching Characteristics						
$t_{d(on)}$	Turn-On Time	V_{DS} = 325 V, I_D = 7A, R_G = 25 Ω (Note 4,5)	--	20	--	ns
t_r	Turn-On Rise Time		--	50	--	ns
$t_{d(off)}$	Turn-Off Delay Time		--	80	--	ns
t_f	Turn-Off Fall Time		--	70	--	ns
Q_g	Total Gate Charge	V_{DS} = 520 V, I_D = 7A, V_{GS} = 10 V (Note 4,5)	--	29	--	nC
Q_{gs}	Gate-Source Charge		--	4.7	--	nC
Q_{gd}	Gate-Drain Charge		--	12.5	--	nC
Source-Drain Diode Maximum Ratings and Characteristics						
I_S	Continuous Source-Drain Diode Forward Current		--	--	7	A
I_{SM}	Pulsed Source-Drain Diode Forward Current		--	--	30	
V_{SD}	Source-Drain Diode Forward Voltage	I_S = 7A, V_{GS} = 0 V	--	--	1.4	V
t_{rr}	Reverse Recovery Time	I_S =7A, V_{GS} = 0 V di$_F$/dt = 100 A/µs (Note 4)	--	350	--	ns
Q_{rr}	Reverse Recovery Charge		--	3.3	--	uC

NOTES:
1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. L=10mH, I_{AS}=7A, V_{DD}=50V, R_G=25 Ω,Starting TJ=25 ℃
3. I_{SD}≤7A, di/dt ≤ 200A/us, V_{DD} ≤ BV_{DSS}, Starting TJ = 25 ℃
4. Pulse Test: Pulse width ≤ 300us, Duty Cycle ≤ 2%
5. Essentially Independent of Operating Temperature Typical Characteristics
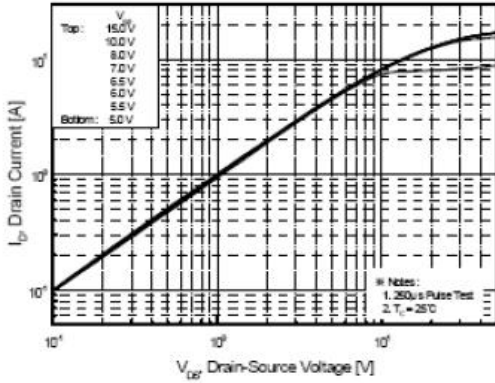
Typical Characteristics
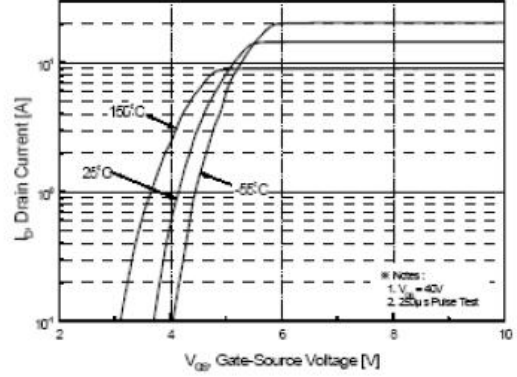

Figure 1. On-Region Characteristics
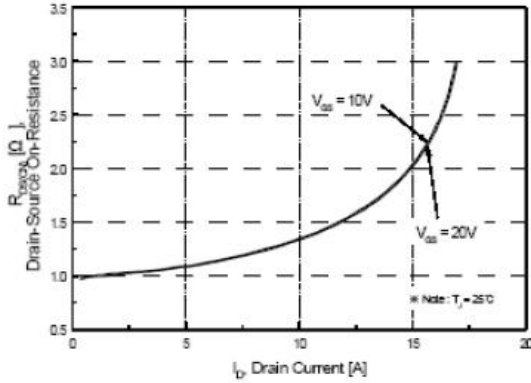

Figure 2. Transfer Characteristics

Figure 3. On-Resistance Variation vs
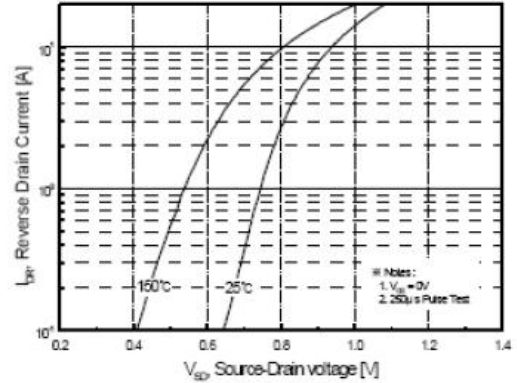Drain Current and Gate Voltage

Figure 4. Body Diode Forward Voltage
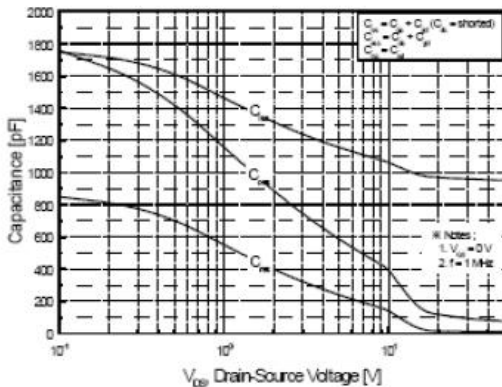Variation with Source Current
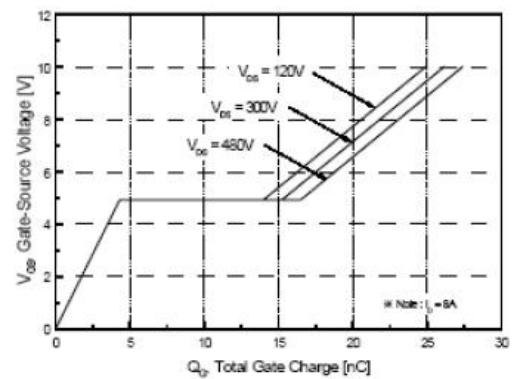and Temperature

Figure 5. Capacitance Characteristics

Figure 6. Gate Charge Characteristics
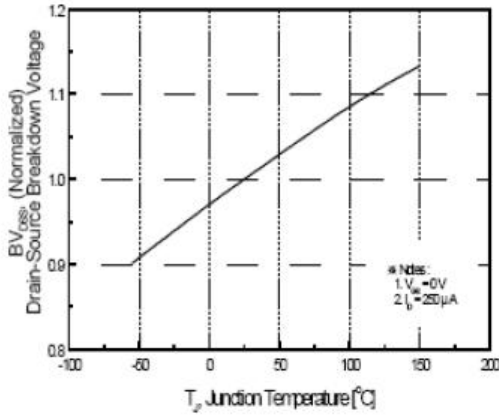
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Typical Characteristics

Figure 7. Breakdown Voltage Variation
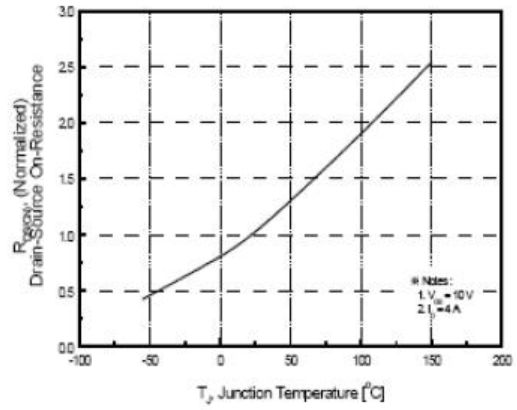vs Temperature

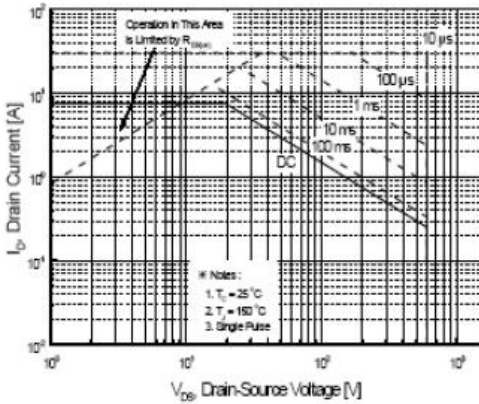Figure 8. On-Resistance Variation
vs Temperature

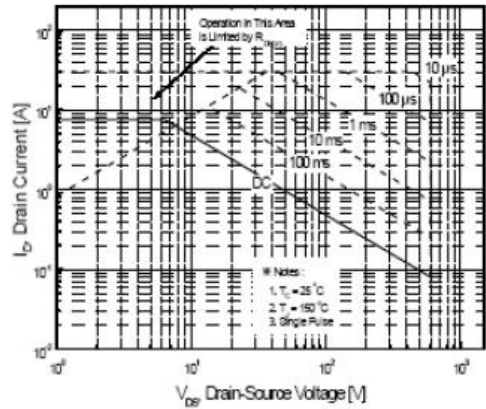Figure 9-1. Maximum Safe Operating Area
for TSP7N65M

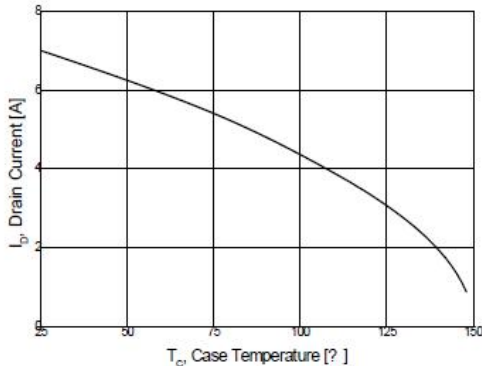Figure 9-2. Maximum Safe Operating Area
for TSF7N65M

Figure 10. Maximum Drain Current
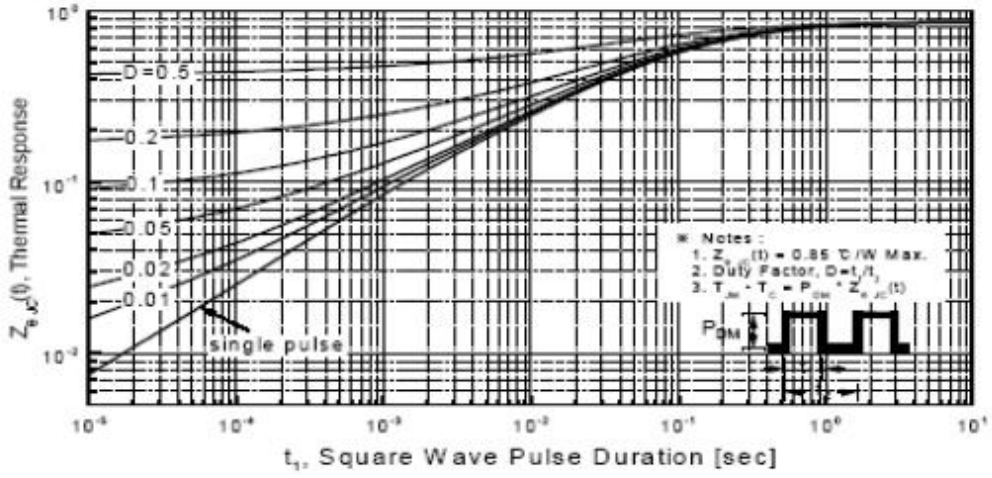vs Case Temperature

Typical Characteristics

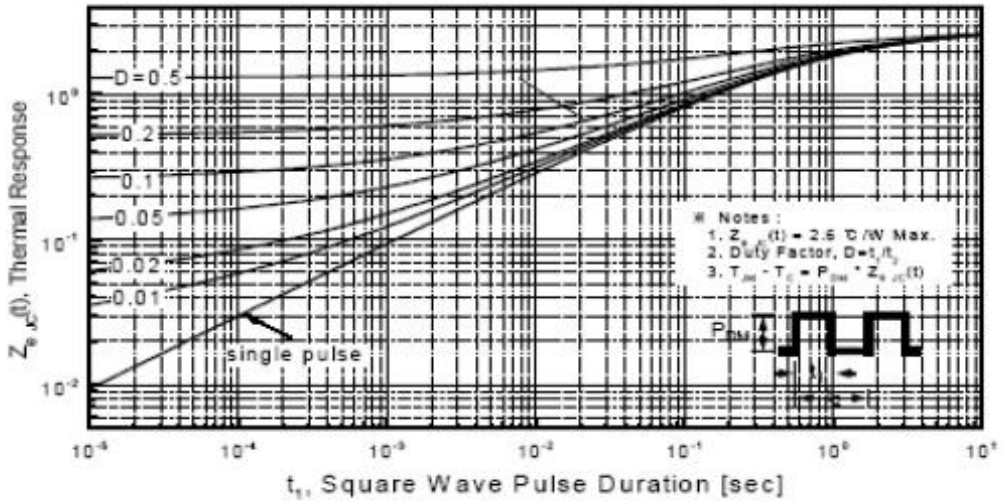**Figure 11-1. Transient Thermal Response Curve for TSP7N65M**

Figure 11-2. Transient Thermal Response Curve for TSF7N65M
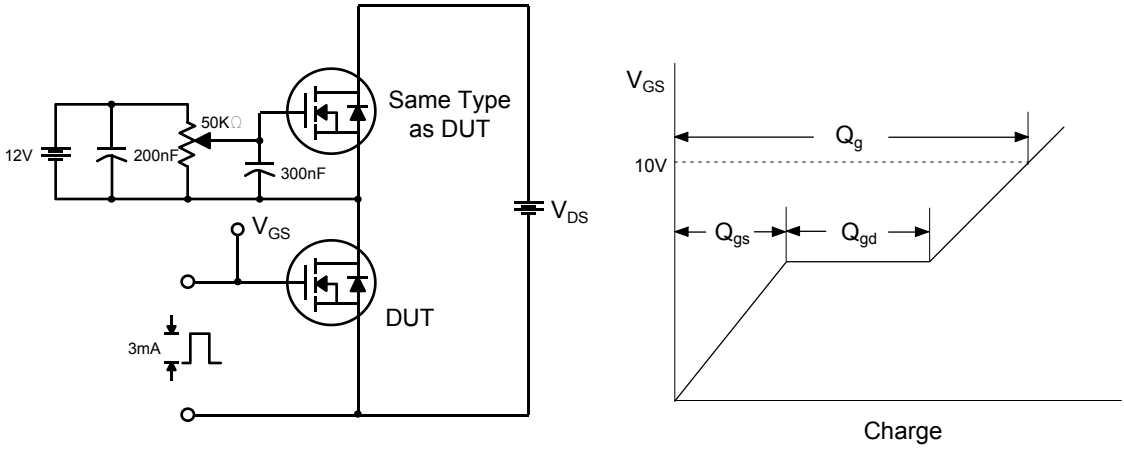
Fig 12. Gate Charge Test Circuit & Waveform

12V | 200nF | 50KΩ | 300nF | Same Type as DUT

V_{GS}

3mA | DUT | V_{DS}

V_{GS}

10V

Q_g

Q_{gs} | Q_{gd}

Charge

Fig 13. Resistive Switching Test Circuit & Waveforms

V_{DS} | R_L

R_G | V_{DD} (0.5 rated V_{DS})

10V | DUT

V_{DS} | 90%

V_{in} | 10%

$t_{d(on)}$ | t_r | $t_{d(off)}$ | t_f

t_{on} | t_{off}
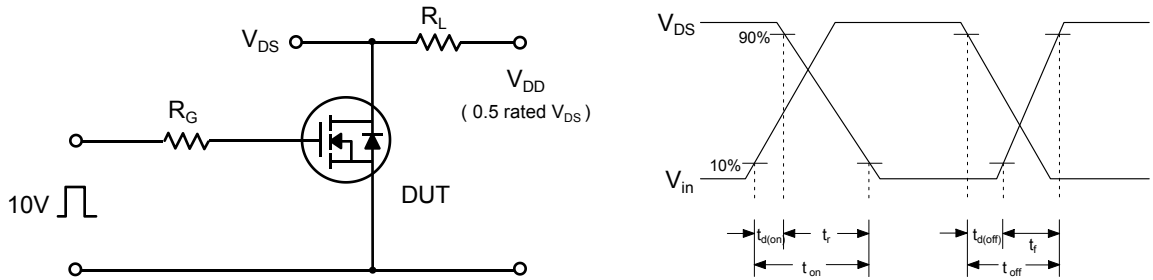
Fig 14. Unclamped Inductive Switching Test Circuit & Waveforms

V_{DS} | L | V_{DD}

I_D

R_G

10V | DUT

$$E_{AS} = \frac{1}{2} L_L I_{AS}^2$$

BV_{DSS}

I_{AS}

$I_D(t)$

V_{DD} | $V_{DS}(t)$

t_p | Time
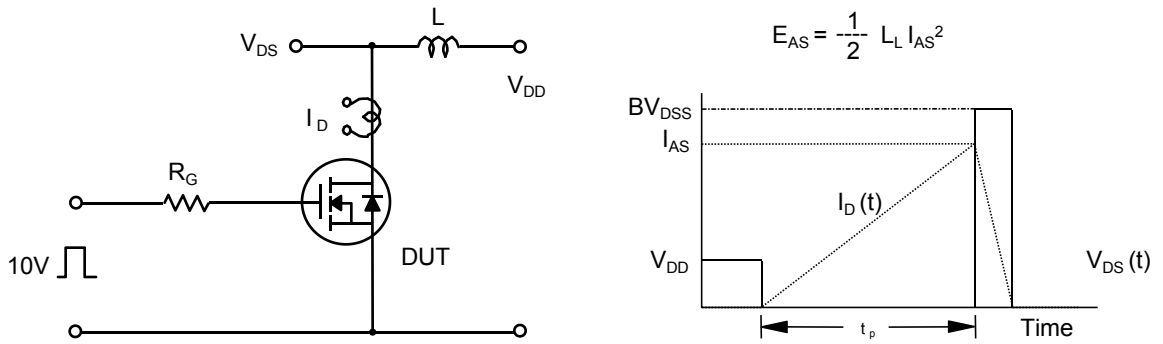
Fig 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

DUT

+

V_{DS}

−

I_S

L

Driver

R_G

Same Type
as DUT

V_{DD}

V_{GS}

• dv/dt controlled by R_G
• I_S controlled by pulse period

V_{GS}
(Driver)

$$D = \frac{\text{Gate Pulse Width}}{\text{Gate Pulse Period}}$$

10V

I_S
(DUT)

I_{FM} , Body Diode Forward Current

di/dt

I_{RM}

Body Diode Reverse Current

V_{DS}
(DUT)

Body Diode Recovery dv/dt

V_f

V_{DD}

Body Diode
Forward Voltage Drop

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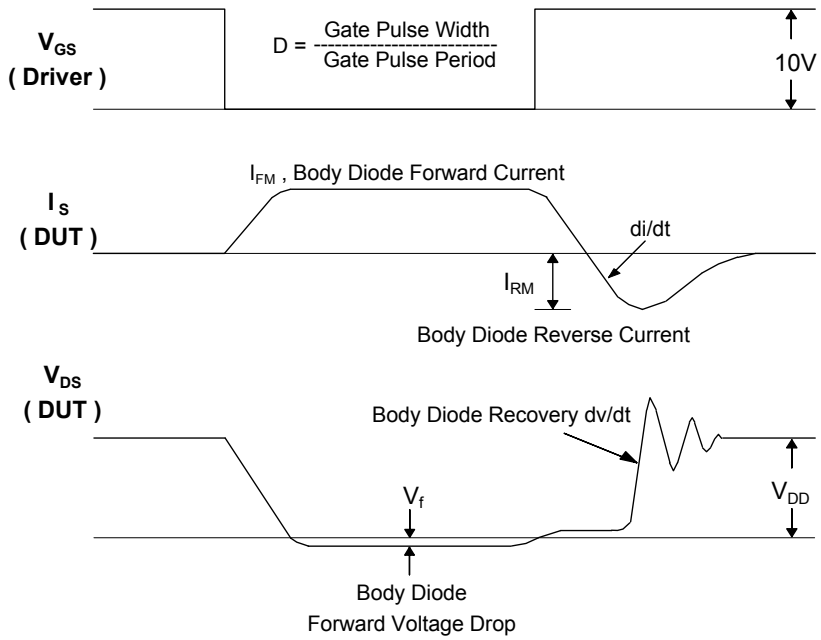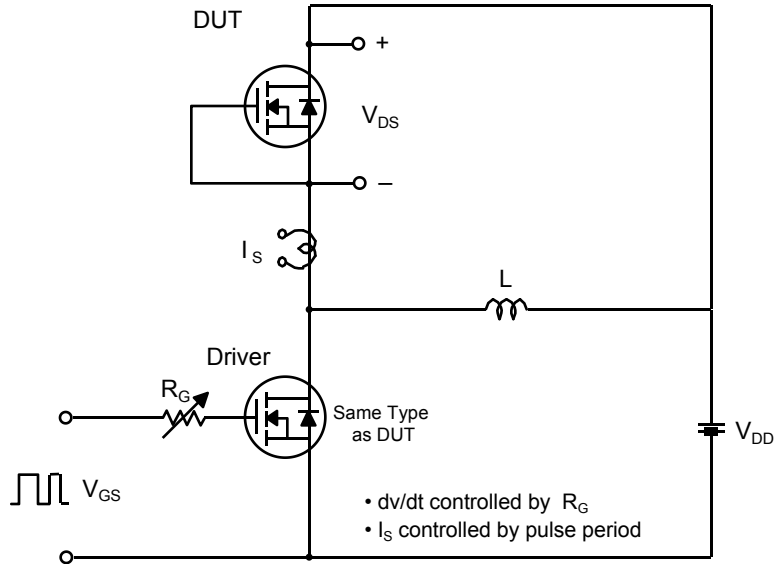
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